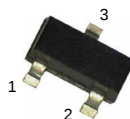


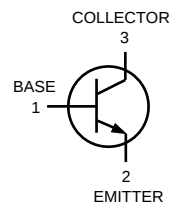
General Purpose Transistor

NPN Silicon

BC848A,B,C



SOT-23



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	30	V _{dc}
Collector-Base Voltage	V _{CB0}	30	V _{dc}
Emitter-Base Voltage	V _{EB0}	5.0	V _{dc}
Collector Current-Continuous	I _c	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max.	Unit
Total Device Dissipation FR-5 Board ⁽¹⁾ T _A =25°C Derate above 25°C	P _D	225 1.8	mW mW / °C
Thermal Resistance Junction to Ambient	R _{θJA}	556	°C / W
Total Device Dissipation Alumina Substrate, ⁽²⁾ T _A =25°C Derate above 25°C	P _D	300 2.4	mW mW / °C
Thermal Resistance Junction to Ambient	R _{θJA}	417	°C / W
Junction and Storage Temperature	T _J ,T _{STG}	-55 to +150	°C

DEVICE MARKING

BC848A=1J; BC848B=1K; BC848C=1L

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdowe Voltage (I _C =10mA)	V _{(BR)CEO}	30	-	-	V _{dc}
Collector-Emitter Breakdowe Voltage (I _C =10 uA, V _{EB} =0)	V _{(BR)CES}	30	-	-	V _{dc}
Collector-Base Breakdowe Voltage (I _C =10 uA)	V _{(BR)CBO}	30	-	-	V _{dc}
Emitter-Base Breakdowe Voltage (I _E =1.0 uA)	V _{(BR)EBO}	5.0	-	-	V _{dc}
Collector Cutoff Current (V _{CB} =30 V) (V _{CB} =30 V, T _A = 150°C)	I _{CBO}	- -	- -	15 5.0	nAdc uAdc

(1) FR-5=1.0 x 0.75 x 0.062in.

(2) Alumina=0.4 x 0.3 x 0.024in. 99.5% alumina.

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted) (Continued)

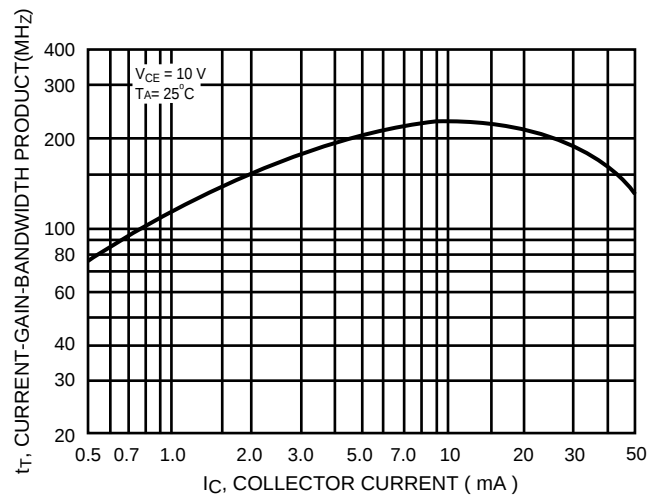
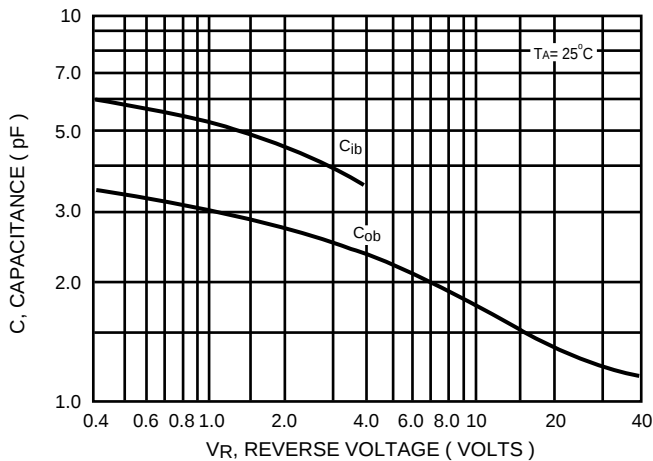
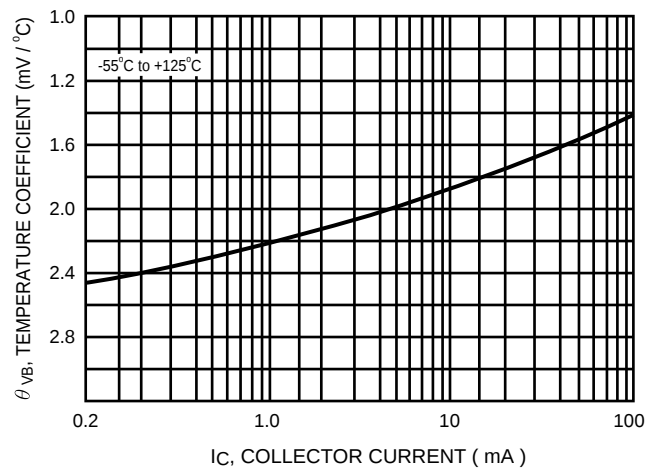
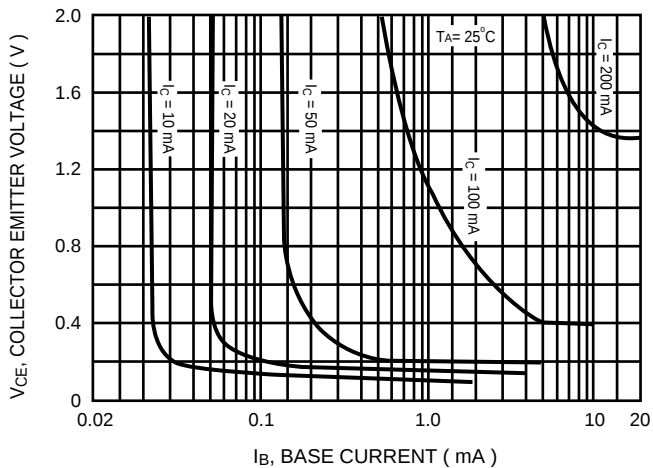
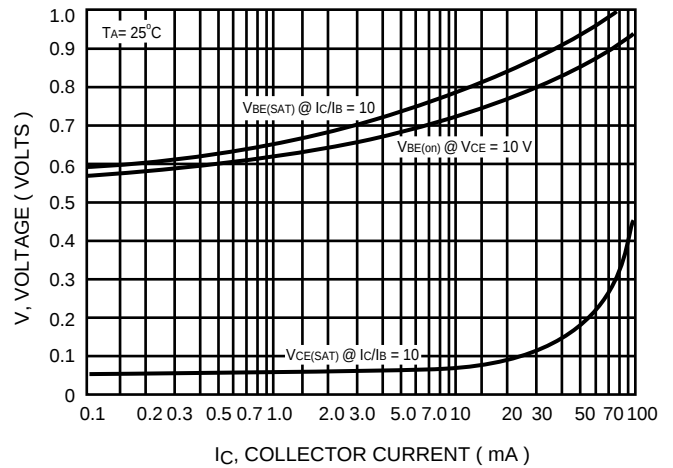
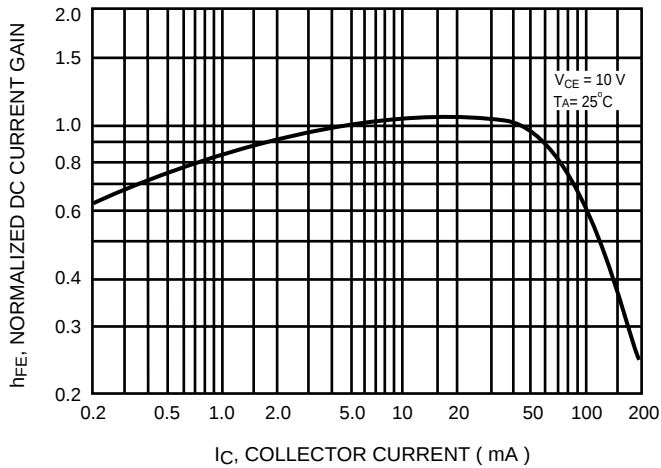
Characteristic	Symbol	Min.	Typ.	Max.	Unit
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ON CHARACTERISTICS

DC Current Gain (IC= 10 μ A, VCE= 5.0 V) (IC= 2.0 mA, VCE= 5.0 V)	BC848A	-	90	-	-
	BC848B	-	150	-	
	BC848C	-	270	-	
	BC848A	110	180	220	
	BC848B	200	290	450	
	BC848C	420	520	800	
Collector-Emitter Saturation Voltage (IC= 10 mA, IB= 0.5 mA) (IC= 100 mA, IB= 5.0 mA)	VCE(sat)	-	-	0.25	V
		-	-	0.60	
Base-Emitter Saturation Voltage (IC= 10 mA, IB= 0.5 mA) (IC= 100 mA, IB= 5.0 mA)	VBE(sat)	-	0.7	-	V
		-	0.9	-	
Base-Emitter Voltage (IC= 2.0 mA, VCE= 5.0 V) (IC= 10 mA, VCE= 5.0 V)	VBE(on)	580	660	700	mV
		-	-	770	

SMALL-SIGNAL CHARACTERISTIC

Current-Gain-Bandwidth Product (IC= 10 mA, VCE= 5.0 V, f=100 MHz)	f _T	100	-	-	MHz
Output Capacitance (VCB= 10 V, f=1.0 MHz)	C _{obo}	-	-	4.5	pF
Noise Figure (VCE= 5.0 Vdc, IC= 0.2 mA, RS= 2.0k ohms, f=1.0 kHz, BW = 200Hz)	NF	-	-	10	dB



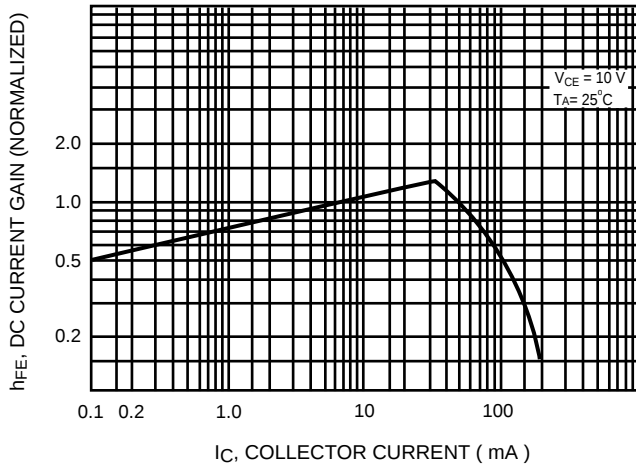


Figure 7. DC Current Gain

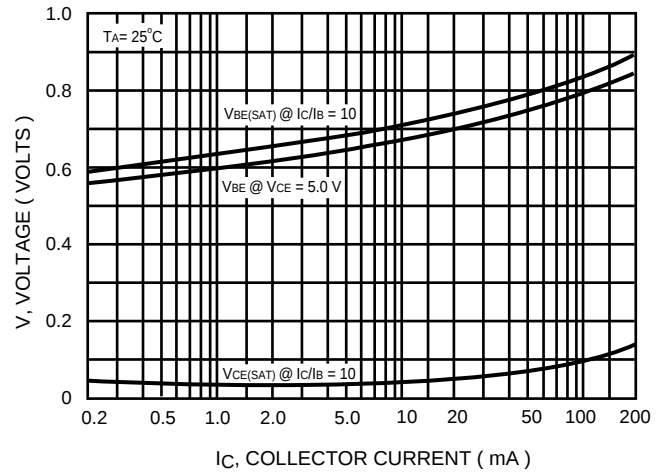


Figure 8. "On" Voltage

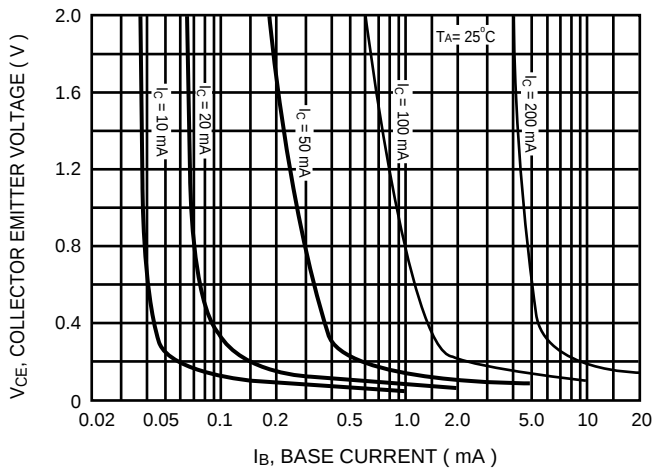


Figure 9. Collector Saturation Region

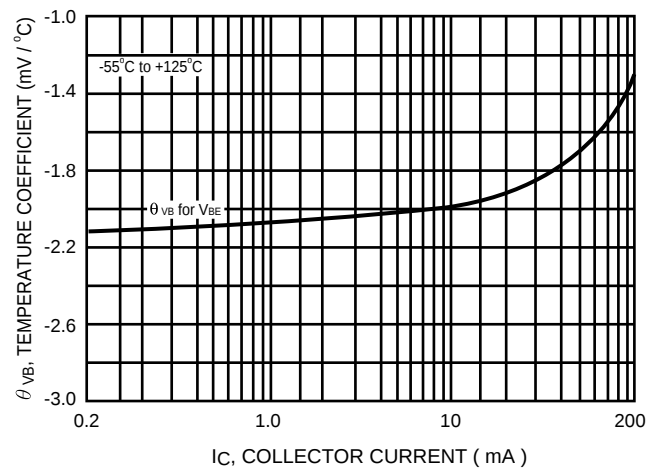


Figure 10. Base-Emitter Temperature Coefficient

